

ABSTRACT OF THE DISCLOSURE

A method of cleaning semiconductor wafers before the epitaxial deposition comprising (A) etching silicon wafers with HF; (B) rinsing the etched wafers with ozonated ultrapure water; (C) treating the rinsed wafers with dilute SC1; (D) rinsing the treated wafers; (E) treating the wafers with
5 dilute HF; (F) rinsing the wafers with DI water; (G) drying the wafers with nitrogen and a trace amount of IPA; wherein steps (E) through (G) are conducted in a single dryer chamber and wafers are not removed from the chamber between steps. A system comprising a single tank adapted for cleaning, etching, rinsing, and drying the wafers has means to inject HF into a DI water stream.